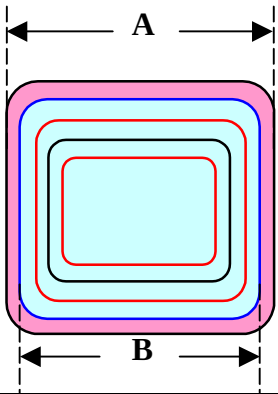


Features : * Extremely low forward volts * Guard ring protection * Low reverse leakage current 	Chip size(A):	1.524* 1.524 mm ²		
	Bond Pad size(B) :	1.422 *1.422 mm ²		
	Thickness :	300μm ± 20μm		
	Metalization :	Anode Ti/Ni/Ag		
	Metalization :	Cathode Ti/Ni/Ag		
Electrical Characteristics	Sym.	Spec. Limit	Unit	
Maximum Instantaneous Forward Volt at IF : 3.0Amp. 25°C	VF max	0.48	Volt	
Minimum Instantaneous Reverse Voltage at IR : 300 uA 25°C	VR min.	43	Volt.	
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	80	Amp	
Storage Temperature	TSTG	-65 to +125	°C	

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